

# Pin Configuration:

- 1. Emitter
- 2. Collector
- 3. Base

### Feature:

• NPN Plastic Power Darlington Transistor

# **Absolute Maximum Ratings**

Parameter	Symbol	BD681	Unit	
Collector Base Voltage	V <sub>CBO</sub>	100		
Collector Emitter Voltage	V <sub>CEO</sub>	100	V	
Emitter Base Voltage	V <sub>EBO</sub>	5		
Collector Current	I <sub>C</sub>	4	4 0.1	
Base Current	I <sub>B</sub>	0.1		
Total Power Dissipation at T <sub>a</sub> = 25°C Derate above 25°C	Б	1.25 10	W mW/°C	
Total Power Dissipation at T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	40 0.32	W W/°C	
Operating and Storage Junction Temperature Range	$T_{j},T_{stg}$	-55 to +150	°C	
Thermal Resistance				
Junction to Case	R <sub>th (j-c)</sub>	3.13	°C/W	
Junction to Ambient in Free Air	R <sub>th (j-a)</sub>	100		



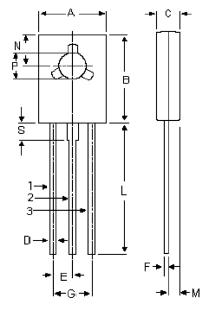
# NPN Power Darlington Transistor **multicomp**



# Electrical Characteristics (T<sub>a</sub> = 25°C unless specified otherwise)

Parameter	Symbol	Test Condition	Min.	Max.	Unit
Collector Emiiter Voltage	V <sub>CEO</sub> *	I <sub>C</sub> = 50mA, I <sub>B</sub> = 0	100	ı	V
Collector Cut off Current	I <sub>CEO</sub>	$V_{CE}$ = Half Rated $V_{CEO}$ , $I_B$ = 0 $V_{CB}$ = Rated $V_{CBO}$ , $I_E$ = 0	-	500 0.2	μA mA
	I <sub>CBO</sub>	$V_{CB}$ = Rated $V_{CBO}$ , $I_{E}$ = 0 $T_{C}$ = 100°C		2	mA
Emitter Cut off Current	I <sub>EBO</sub>	$V_{EB} = 5V, I_{C} = 0$	1	2	mA
Collector Emitter Saturation Voltage	V <sub>CE (sat)</sub> *	I <sub>C</sub> = 1.5A, I <sub>B</sub> = 6mA	-	2.5	V
Base Emitter On Voltage	V <sub>EB (on)</sub> *	I <sub>C</sub> = 1.5A, V <sub>CE</sub> = 3V	-	2.5	V
DC Current Gain	h <sub>FE</sub> *	I <sub>C</sub> = 1.5A, V <sub>CE</sub> = 3V	750	-	-
Small Signal Current Gain	h <sub>fe</sub>	I <sub>C</sub> = 1.5A, V <sub>CE</sub> = 3V f = 1MHz	1	-	-

<sup>\*</sup>Pulse Test : Pulse Width = ≤300µs, Duty Cycle = ≤2%.



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Dimensions	Minimum	Maximum	
А	7.4	7.8	
В	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
E	2.25 (Typical)		
F	0.49	0.75	
G	4.5 (Typical)		
L	15.7 (Typical)		
M	1.27 (Typical)		
N	3.75 (Typical)		
Р	3 3.2		
S	2.5 (Typical)		

**Dimensions: Millimetres** 

### **Part Number Table**

Description	Part Number		
Darlington Transistor, TO-126	BD681		

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